Silicon PNP Power Transistors 2SA1184

DESCRIPTION

·With TO-126 package
·High breakdown voltage

APPLICATIONS

·Audio frequency power amplifier
·High frequency power amplifier

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

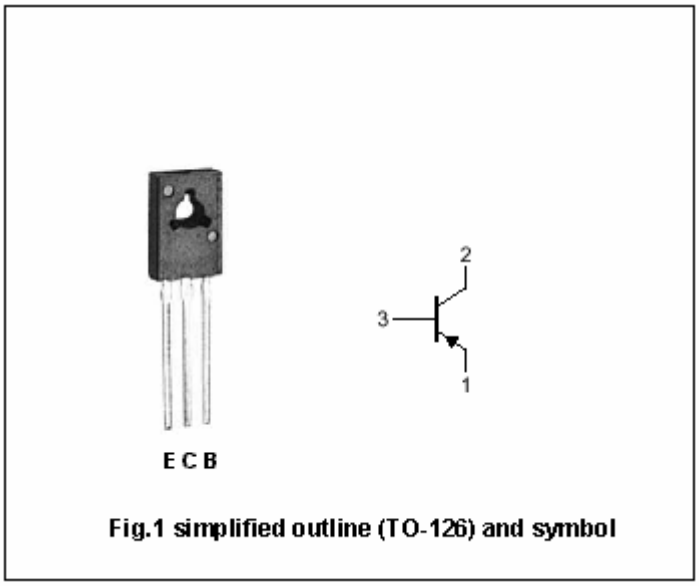

Fig.1 simplified outline (TO-126) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-120	V
V_{CEO}	Collector-emitter voltage	Open base	-120	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-1	A
I_B	Base current		-0.1	A
P_D	Total power dissipation	T_a=25□	1.5	W
		T_C=25□	15	
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55□+150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-10mA; I_B=0	-120			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=-10μA; I_C=0	-5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-500mA; I_B=-50mA			-1.0	V
V_{BE}	Base-emitter on voltage	I_C=-500mA ; V_{CE}=-5V			-1.0	V
I_{CBO}	Collector cut-off current	V_{CB}=-120V; I_E=0			-1	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-1	μA
h_{FE}	DC current gain	I_C=-100mA ; V_{CE}=-5V	80		240	
f_T	Transition frequency	I_C=-0.1A ; V_{CE}=5V		120		MHz

PACKAGE OUTLINE

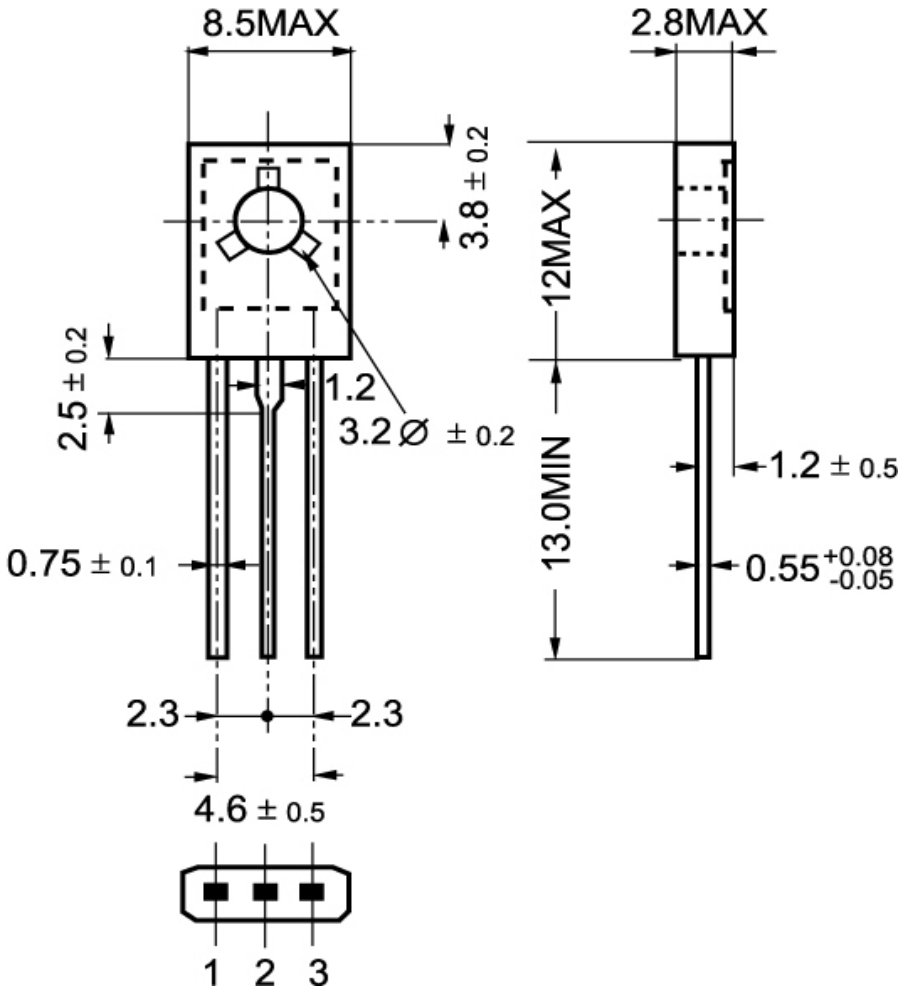

Fig.2 Outline dimensions